

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		lateral\$4 near7 (MOS\$4 or MOSFET\$1 or NMOS\$4 or PMOS\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 17:59
S1	5	((("4455565") or ("5119149") or ("5243234") or ("5252848") or ("5918137"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/03/15 10:51
S2	2	((("5406110") or ("5306652"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/03/15 14:00
S3	7383	lateral\$4 adj8 (FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$4 adj gate adj field adj effect adj transistor\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:44
S4	140917	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:47
S5	152308	(gate\$1 or electrode\$1) and source\$1 and drain\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:48
S6	18145	LDD\$1 or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:49
S7	494	S3 and S4 and S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:50
S8	1299	S3 and S4 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:58
S9	16110	(source\$1 or drain\$1) with (gate\$1 or electrode\$1) with (distance or length or width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 15:01

EAST Search History

S10	137	S7 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 15:02
S11	718	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:32
S12	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:32
S13	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:32
S14	736	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 16:09
S15	17987	LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:44
S16	103	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) and (LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4-(source\$1 or drain\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 16:15

EAST Search History

S17	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:34
S18	74	lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:34
S19	0	lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconductor\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:38
S20	177	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:38
S21	0	lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:38
S22	716	(LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 17:07

EAST Search History

S23	497	(LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))) and ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 17:08
S24	152128	(gate\$1 or electrode\$1) and source\$1 and drain\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:45
S25	140632	(field adj (oxide or isolat\$5)) or LOCOS or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 17:29
S26	197	((LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))) and ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide or isolat\$5)) or LOCOS or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 17:14

EAST Search History

S27	140776	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:45
S28	249	lateral\$4 near7 (metal adj oxide adj semiconduct\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:40
S29	2317	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:41
S30	3309	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) or ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1))) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 18:02

EAST Search History

S31	991	(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) or ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1))) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1))) and (LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 18:03
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EAST Search History

S32	531	(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) or ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1))) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1))) and (LDD or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1)))) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 18:03
S33	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:42
S34	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:43

EAST Search History

S35	2371	(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) or ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1))) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 18:33
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EAST Search History

S36	1176	(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) or ((LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1))) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1)) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/13 18:34
S37	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:33
S38	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:33
S39	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:33

EAST Search History

S40	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:34
S41	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:37
S42	0	lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconductor\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:38
S43	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:39
S44	0	lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:39
S45	249	lateral\$4 near7 (metal adj oxide adj semiconductor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:40
S46	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:41
S47	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:42
S48	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:43

EAST Search History

S49	18145	LDD\$1 or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:47
S50	152308	(gate\$1 or electrode\$1) and source\$1 and drain\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:46
S51	140917	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/15 14:46
S52	3315	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4. adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 13:14

EAST Search History

S53	533	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1))) and (LDD\$1 or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:50
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EAST Search History

S54	73	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1))) and (LDD\$1 or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 11:51
S55	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 13:13

EAST Search History

S56	3486	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 13:14
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EAST Search History

S57	547	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or (LD adj LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1))) and (LDD\$1 or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 13:16
S58	387	(438/286).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/03/14 16:16

EAST Search History

S59	40	(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj diffus\$5 adj double adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj double adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1))) and (LDD\$1 or "LDD" or ((light\$3 adj dop\$3) adj (source\$1 or drain\$1)) or (lightly-doped adj (source\$1 or drain\$1)) or ((shallow or extension\$1) near4 (source\$1 or drain\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))) and (("438/286"). CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/03/14 16:17
S60	1	("6255154").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/03/14 18:21
S61	0	"6255154".URPN.	US-PGPUB; USPAT	OR	OFF	2002/03/14 18:20

EAST Search History

S62	9	((("5382536") or ("5517046") or ("5541435") or ("5578514") or ("5844272") or ("5854566") or ("5869371") or ("6033948") or ("6051482"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/03/14 18:23
S63	1	("5541123").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/03/14 19:11
S64	42	((("4918026") or ("5229308") or ("5242841") or ("5306652") or ("5306656") or ("5322804") or ("5348895") or ("5366916") or ("5482888") or ("5510275") or ("5512495") or ("5514608") or ("5521105") or ("5548147") or ("5578514") or ("5777363") or ("5907173") or ("5917222") or ("6001710") or ("6025231") or ("6037226") or ("6063671") or ("6063674") or ("6117738") or ("6153451") or ("6177321") or ("6207518") or ("6211552") or ("6255154") or ("6258670") or ("6258674") or ("6424005") or ("6441431") or ("6483149") or ("6506641") or ("6531355") or ("6559019") or ("6599782") or ("6613633") or ("6635925") or ("20020182810") or ("20030127689"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/04/22 11:09
S65	1	("4981550").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/22 12:25

EAST Search History

S66	42	((("5348895") or ("6025231") or ("6255154") or ("6599782") or ("6531355") or ("6613633") or ("4918026") or ("5229308") or ("5242841") or ("5306652") or ("5306656") or ("5322804") or ("5366916") or ("5482888") or ("5510275") or ("5512495") or ("5514608") or ("5521105") or ("5548147") or ("5578514") or ("5777363") or ("5907173") or ("5917222") or ("6001710") or ("6037226") or ("6063671") or ("6063674") or ("6117738") or ("6153451") or ("6177321") or ("6207518") or ("6211552") or ("6258670") or ("6258674") or ("6424005") or ("6441431") or ("6483149") or ("6506641") or ("6559019") or ("6635925") or ("20020182810") or ("20030127689")).PN.	US-PGPUB; USPAT	OR	OFF	2006/02/21 08:23
S67	1	("6528850").PN.	US-PGPUB; USPAT	OR	OFF	2006/02/21 09:15
S68	1	("4963973").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/21 09:15
S69	146	RESURF	JPO; DERWENT	OR	OFF	2006/02/22 11:17
S70	31	LD near4 MOS	JPO; DERWENT	OR	OFF	2006/02/22 11:31
S71	2	S69 and S70	JPO; DERWENT	OR	OFF	2006/02/22 11:17
S72	1	("5627394").PN.	US-PGPUB; USPAT	OR	OFF	2006/02/22 11:31
S73	4	("5306652" "5406110" "5429959" "5502323").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/22 11:31
S74	9	("5627394").URPN.	USPAT	OR	OFF	2006/02/22 11:50
S75	1468	((257/335) or (257/336) or (257/337) or (257/493)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/22 11:53
S76	17	("5406110").URPN.	USPAT	OR	OFF	2006/02/22 12:03
S77	13	("5841166").URPN.	USPAT	OR	OFF	2006/02/22 12:15